

Title (en)

ELECTRIC SEMICONDUCTOR ELEMENT WITH A CONTACT HOLE

Title (de)

ELEKTRISCHES HALBLEITERBAUELEMENT MIT EINEM KONTAKTLOCH

Title (fr)

COMPOSANT ELECTRIQUE A SEMICONDUCTEUR PRESENTANT UN TROU DE CONTACT

Publication

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Application

**EP 00958104 A 20000703**

Priority

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Abstract (en)

[origin: DE19930797A1] An electric semiconductor element comprising a monocrystalline semiconductor substrate which is made, for example, out of silicon; an insulating layer (6) which is penetrated by a contact hole (30) on at least one point and arranged on the surface of the semiconductor substrate (1); in addition to a contact element which comes into contact with the semiconductor substrate (1) by means of the contact hole (30) and which is made of a material such as aluminium, whereby the semiconductor material of the substrate can be dissolved in an anisotropic process. The edges of the contact hole (30) are configured as diffusion-preventing structures.

IPC 1-7

**H01L 29/41**; **H01L 21/28**

IPC 8 full level

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CPC (source: EP US)

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